Notice of References Cited

Application/Control No. 10/720,035	Applicant(s)/Patent Under Reexamination TSANG ET AL.		
Examiner	Art Unit		
Daniel L. Greene Jr.	3663	Page 1 of 2	

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	Α	US-5,082,505	01-1992	Cota et al.	136/253
*	В	US-5,606,213	02-1997	Kherani et al.	310/303
*	С	US-5,260,621	11-1993	Little et al.	310/303
*	D	US-3,344,289	09-1967	KNIGHT ROBERT D	310/301
*	Ε	US-4,024,420	05-1977	Anthony et al.	310/303
*	F	US-4,010,534	03-1977	Anthony et al.	438/19
*	G	US-2,900,535	08-1959	ALEXANDER THOMAS	310/302
*	Н	US-6,949,865	09-2005	Gadeken, Larry	310/303
*	_	US-4,169,917	10-1979	Baker et al.	429/26
	7	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	S					
	Т					·

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Metal-Semiconductor Ohmic and Schottky Contacts, Brigham Young University, available @ http://www.ee.byu.edu/cleanroom/ohmic-schottky.phtml, last accessed 11/14/2005
	V	Denninger, Schottky Contacts, Semiconductor physics 1, WS 2001/2002 Denninger, available @ http://www.ee.sc.edu/research/SiC_Research/papers/schottkycontacts.pdf,last accessed 11/14/2005
	w	Godlevsky et al., Ab Initio Molecular Dynamics Simulation of Liquid CdTe and GaAs: ☐☐Semiconducting versus Metallic Behavior, Department of Chemical Engineering and Materials Science, Minnesota Supercomputer Institute, University of Minnesota, 13 May 1998
	x	Yu et al., Molecular-dynamics study of surface segregation in liquid semiconductor alloys, Department of Physics, The Ohio State University, Columbus, Ohio, 16 May 1997

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Notice of References Cited

Application/Control No. 10/720,035	Applicant(s)/Patent Under Reexamination TSANG ET AL.		
Examiner	Art Unit		
Daniel I. Greene Jr	3663	Page 2 of 2	

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-			
	В	US-			
	С	US-			
	D	US-			
	Е	US-			
	F	US-			
	G	US-		V .	
	Н	US-			
	ı	US-			
	J	US-		·	
	Κ	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	Ν					
	0					
	Р					
	Ø					
	R					
	S					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	υ	Price et al., Rotator Phases in Narrow-Gap Semiconductors, Argonne National Laboratory, 12/1993
	٧	Kulkami et al., Ab initio molecular-dynamics study of the structural and transport properties of liquid germanium, Department of Physics, The Ohio State University, Columbus, Ohio, 23 September 1996
	w	Matthiesen et al., Diffusion Processes in Molten Semiconductors, 3/2002, available @ http://zeta.lerc.nasa.gov/expr3/dpims.htm, last accessed 11/15/05
	х	Enderby et al., Liquid Semiconductors, Rep. Prog. Phys. 53 (1990) 85-179. Printed in the UK, available @ http://ej.iop.org/links/q48/dryRcZ58u8dN,T6YTA2whQ/rpv53i2p85.pdf, last accessed 11/14/05

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.